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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I ² C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I ² S, POR, PWM, WDT
Number of I/O	119
Program Memory Size	576KB (576K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	50K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 24x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-144-4
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xe167fm72f80laakxqma1

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



General Device Information

Table	e 5 Pin De	finitior	ns and	Functions (cont'd)			
Pin	Symbol	Ctrl.	Туре	Function			
5	P8.4	O0 / I	St/B	Bit 4 of Port 8, General Purpose Input/Output			
	CCU60_COU T61	01	St/B	CCU60 Channel 1 Output			
	CCU62_CC6 1	02	St/B	CCU62 Channel 1 Output			
	TMS_D	IH	St/B	JTAG Test Mode Selection Input If JTAG pos. D is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it.			
	CCU62_CC6 1INB	I	St/B	CCU62 Channel 1 Input			
6	TRST	1	In/B	Test-System Reset Input For normal system operation, pin TRST should be held low. A high level at this pin at the rising edge of PORST activates the XE167xM's debug system. In this case, pin TRST must be driven low once to reset the debug system. An internal pull-down device will hold this pin low when nothing is driving it.			
7	P8.3	O0 / I	St/B	Bit 3 of Port 8, General Purpose Input/Output			
	CCU60_COU T60	01	St/B	CCU60 Channel 0 Output			
	CCU62_CC6 0	O2	St/B	CCU62 Channel 0 Output			
	TDI_D	IH	St/B	JTAG Test Data Input If JTAG pos. D is selected during start-up, an internal pull-up device will hold this pin low when nothing is driving it.			
	CCU62_CC6 0INB	I	St/B	CCU62 Channel 0 Input			



General Device Information

Table	e 5 Pin De	finitior	ns and	Functions (cont'd)
Pin	Symbol	Ctrl.	Туре	Function
63	P4.1	O0 / I	St/B	Bit 1 of Port 4, General Purpose Input/Output
	U3C0_SELO 3	O1	St/B	USIC3 Channel Select/Control 3 Output
	TxDC2	02	St/B	CAN Node 2 Transmit Data Output
	CC2_CC25	O3 / I	St/B	CAPCOM2 CC25IO Capture Inp./ Compare Out.
	CS1	OH	St/B	External Bus Interface Chip Select 1 Output
	CCU62_CCP OS0B	I	St/B	CCU62 Position Input 0
	T4EUDB	I	St/B	GPT12E Timer T4 External Up/Down Control Input
	ESR1_8	I	St/B	ESR1 Trigger Input 8
64	P2.4	O0 / I	St/B	Bit 4 of Port 2, General Purpose Input/Output
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output
	TxDC0	02	St/B	CAN Node 0 Transmit Data Output
	CC2_CC17	O3 / I	St/B	CAPCOM2 CC17IO Capture Inp./ Compare Out.
	A17	OH	St/B	External Bus Interface Address Line 17
	ESR1_0	I	St/B	ESR1 Trigger Input 0
	U0C0_DX0F	I	St/B	USIC0 Channel 0 Shift Data Input
	RxDC1A	I	St/B	CAN Node 1 Receive Data Input
65	P11.1	O0 / I	St/B	Bit 1 of Port 11, General Purpose Input/Output
	CCU61_COU T61	O1	St/B	CCU61 Channel 1 Output
	TxDC0	02	St/B	CAN Node 0 Transmit Data Output
	U3C1_SELO 0	O3	St/B	USIC3 Channel 1 Select/Control 0 Output
	CCU63_CCP OS1A	I	St/B	CCU63 Position Input 1
	CCU61_CTR APD	I	St/B	CCU61 Emergency Trap Input
	U3C1_DX2A	I	St/B	USIC3 Channel 1 Shift Control Input



General Device Information

Table	e 5 Pin De	finition	is and	Functions (cont'd)
Pin	Symbol	Ctrl.	Туре	Function
117	P10.10	O0 / I	St/B	Bit 10 of Port 10, General Purpose Input/Output
	U0C0_SELO 0	01	St/B	USIC0 Channel 0 Select/Control 0 Output
	CCU60_COU T63	02	St/B	CCU60 Channel 3 Output
	AD10	OH / IH	St/B	External Bus Interface Address/Data Line 10
	U0C0_DX2C	I	St/B	USIC0 Channel 0 Shift Control Input
	U0C1_DX1A	I	St/B	USIC0 Channel 1 Shift Clock Input
	TDI_B	IH	St/B	JTAG Test Data Input If JTAG pos. B is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it.
118	P10.11	O0 / I	St/B	Bit 11 of Port 10, General Purpose Input/Output
	U1C0_SCLK OUT	01	St/B	USIC1 Channel 0 Shift Clock Output
	BRKOUT	O2	St/B	OCDS Break Signal Output
	U3C0_SELO 0	O3	St/B	USIC3 Channel 0 Select/Control 0 Output
	AD11	OH / IH	St/B	External Bus Interface Address/Data Line 11
	U1C0_DX1D	I	St/B	USIC1 Channel 0 Shift Clock Input
	RxDC2B	I	St/B	CAN Node 2 Receive Data Input
	TMS_B	IH	St/B	JTAG Test Mode Selection Input If JTAG pos. B is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it.
	U3C0_DX2A	I	St/B	USIC3 Channel 0 Shift Control Input
119	P9.2	O0 / I	St/B	Bit 2 of Port 9, General Purpose Input/Output
	CCU63_CC6 2	01	St/B	CCU63 Channel 2 Output
	CCU63_CC6 2INA	1	St/B	CCU63 Channel 2 Input
	CAPINB	Ι	St/B	GPT12E Register CAPREL Capture Input



3.1 Memory Subsystem and Organization

The memory space of the XE167xM is configured in the von Neumann architecture. In this architecture all internal and external resources, including code memory, data memory, registers and I/O ports, are organized in the same linear address space.

Address Area	Start Loc.	End Loc.	Area Size ²⁾	Notes
IMB register space	FF'FF00 _H	FF'FFFF _H	256 Bytes	-
Reserved (Access trap)	F0'0000 _H	FF'FEFF _H	<1 Mbyte	Minus IMB registers
Reserved for EPSRAM	E8'8000 _H	EF'FFFF _H	480 Kbytes	Mirrors EPSRAM
Emulated PSRAM	E8'0000 _H	E8'7FFF _H	32 Kbytes	With Flash timing
Reserved for PSRAM	E0'8000 _H	E7'FFFF _H	480 Kbytes	Mirrors PSRAM
Program SRAM	E0'0000 _H	E0'7FFF _H	32 Kbytes	Maximum speed
Reserved for Flash	CD'0000 _H	DF'FFFF _H	<1.25 Mbytes	-
Program Flash 3	CC'0000 _H	CC'FFFF _H	64 Kbytes	-
Program Flash 2	C8'0000 _H	CB'FFFF _H	256 Kbytes	-
Program Flash 1	C4'0000 _H	C7'FFFF _H	256 Kbytes	-
Program Flash 0	C0'0000 _H	C3'FFFF _H	256 Kbytes	3)
External memory area	40'0000 _H	BF'FFFF _H	8 Mbytes	-
Available Ext. IO area ⁴⁾	21'0000 _H	3F'FFFF _H	< 2 Mbytes	Minus USIC/CAN
Reserved	20'BC00 _H	20'FFFF _H	17 Kbytes	-
USIC alternate regs.	20'B000 _H	20'BFFF _H	4 Kbytes	Accessed via EBC
MultiCAN alternate regs.	20'8000 _H	20'AFFF _H	12 Kbytes	Accessed via EBC
Reserved	20'6000 _H	20'7FFF _H	8 Kbytes	-
USIC registers	20'4000 _H	20'5FFF _H	8 Kbytes	Accessed via EBC
MultiCAN registers	20'0000 _H	20'3FFF _H	16 Kbytes	Accessed via EBC
External memory area	01'0000 _H	1F'FFFF _H	< 2 Mbytes	Minus segment 0
SFR area	00'FE00 _H	00'FFFF _H	0.5 Kbyte	-
Dual-Port RAM	00'F600 _H	00'FDFF _H	2 Kbytes	-
Reserved for DPRAM	00'F200 _H	00'F5FF _H	1 Kbyte	-
ESFR area	00'F000 _H	00'F1FF _H	0.5 Kbyte	-
XSFR area	00'E000 _H	00'EFFF _H	4 Kbytes	-

Table 7 XE167xM Memory Map ¹⁾



With its maximum resolution of 2 system clock cycles, the **GPT2 module** provides precise event control and time measurement. It includes two timers (T5, T6) and a capture/reload register (CAPREL). Both timers can be clocked with an input clock which is derived from the CPU clock via a programmable prescaler or with external signals. The counting direction (up/down) for each timer can be programmed by software or altered dynamically with an external signal on a port pin (TxEUD). Concatenation of the timers is supported with the output toggle latch (T6OTL) of timer T6, which changes its state on each timer overflow/underflow.

The state of this latch may be used to clock timer T5, and/or it may be output on pin T6OUT. The overflows/underflows of timer T6 can also be used to clock the CAPCOM2 timers and to initiate a reload from the CAPREL register.

The CAPREL register can capture the contents of timer T5 based on an external signal transition on the corresponding port pin (CAPIN); timer T5 may optionally be cleared after the capture procedure. This allows the XE167xM to measure absolute time differences or to perform pulse multiplication without software overhead.

The capture trigger (timer T5 to CAPREL) can also be generated upon transitions of GPT1 timer T3 inputs T3IN and/or T3EUD. This is especially advantageous when T3 operates in Incremental Interface Mode.



3.11 Real Time Clock

The Real Time Clock (RTC) module of the XE167xM can be clocked with a clock signal selected from internal sources or external sources (pins).

The RTC basically consists of a chain of divider blocks:

- Selectable 32:1 and 8:1 dividers (on off)
- The reloadable 16-bit timer T14
- The 32-bit RTC timer block (accessible via registers RTCH and RTCL) consisting of: – a reloadable 10-bit timer
 - a reloadable 6-bit timer
 - a reloadable 6-bit timer
 - a reloadable 10-bit timer

All timers count up. Each timer can generate an interrupt request. All requests are combined to a common node request.

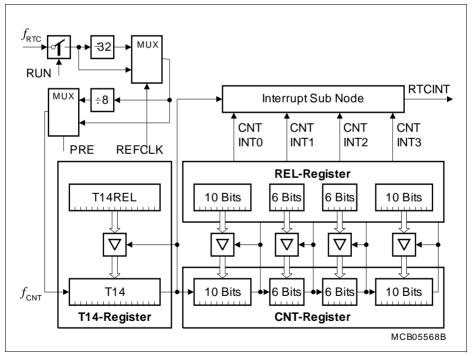


Figure 10 RTC Block Diagram

Note: The registers associated with the RTC are only affected by a power reset.



Table 10 Ir	struction Set Summary (cont'd)	
Mnemonic	Description	Bytes
ROL/ROR	Rotate left/right direct word GPR	2
ASHR	Arithmetic (sign bit) shift right direct word GPR	2
MOV(B)	Move word (byte) data	2/4
MOVBS/Z	Move byte operand to word op. with sign/zero extension	2/4
JMPA/I/R	Jump absolute/indirect/relative if condition is met	4
JMPS	Jump absolute to a code segment	4
JB(C)	Jump relative if direct bit is set (and clear bit)	4
JNB(S)	Jump relative if direct bit is not set (and set bit)	4
CALLA/I/R	Call absolute/indirect/relative subroutine if condition is met	4
CALLS	Call absolute subroutine in any code segment	4
PCALL	Push direct word register onto system stack and call absolute subroutine	4
TRAP	Call interrupt service routine via immediate trap number	2
PUSH/POP	Push/pop direct word register onto/from system stack	2
SCXT	Push direct word register onto system stack and update register with word operand	4
RET(P)	Return from intra-segment subroutine (and pop direct word register from system stack)	2
RETS	Return from inter-segment subroutine	2
RETI	Return from interrupt service subroutine	2
SBRK	Software Break	2
SRST	Software Reset	4
IDLE	Enter Idle Mode	4
PWRDN	Unused instruction ¹⁾	4
SRVWDT	Service Watchdog Timer	4
DISWDT/ENWD	DT Disable/Enable Watchdog Timer	4
EINIT	End-of-Initialization Register Lock	4
ATOMIC	Begin ATOMIC sequence	2
EXTR	Begin EXTended Register sequence	2
EXTP(R)	Begin EXTended Page (and Register) sequence	2/4
EXTS(R)	Begin EXTended Segment (and Register) sequence	2/4

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4 Electrical Parameters

The operating range for the XE167xM is defined by its electrical parameters. For proper operation the specified limits must be respected when integrating the device in its target environment.

4.1 General Parameters

These parameters are valid for all subsequent descriptions, unless otherwise noted.

4.1.1 Absolut Maximum Rating Conditions

Stresses above the values listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for an extended time may affect device reliability.

During absolute maximum rating overload conditions ($V_{\rm IN} > V_{\rm DDP}$ or $V_{\rm IN} < V_{\rm SS}$) the voltage on $V_{\rm DDP}$ pins with respect to ground ($V_{\rm SS}$) must not exceed the values defined by the absolute maximum ratings.

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Output current on a pin when high value is driven	I _{OH} SR	-30	-	-	mA	
Output current on a pin when low value is driven	I _{OL} SR	-	-	30	mA	
Overload current	$I_{\rm OV}{\rm SR}$	-10	-	10	mA	1)
Absolute sum of overload currents	$\Sigma I_{OV} $ SR	-	-	100	mA	1)
Junction Temperature	$T_{\rm J}{\rm SR}$	-40	-	150	°C	
Storage Temperature	$T_{\rm ST}{ m SR}$	-65	-	150	°C	
Digital supply voltage for IO pads and voltage regulators	$V_{ m DDPA}, V_{ m DDPB}$	-0.5	-	6.0	V	
Voltage on any pin with respect to ground (Vss)	$V_{\rm IN}$ SR	-0.5	-	V _{DDP} + 0.5	V	$V_{\rm IN} \leq V_{\rm DDP(max)}$

Table 11 Absolute Maximum Rating Parameters

 Overload condition occurs if the input voltage V_{IN} is out of the absolute maximum rating range. In this case the current must be limited to the listed values by design measures.



4.2.2 DC Parameters for Lower Voltage Area

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV} .

Note: Operating Conditions apply.

 Table 14 is valid under the following conditions:

 $V_{\text{DDP}} \ge 3.0 \text{ V}; V_{\text{DDPtvp}} = 3.3 \text{ V}; V_{\text{DDP}} \le 4.5 \text{ V}$

Parameter	Symbol		Values	5	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Pin capacitance (digital inputs/outputs). To be doubled for double bond pins. ¹⁾	C _{IO} CC	-	-	10	pF	not subject to production test
Input Hysteresis ²⁾	HYS CC	$0.07 ext{ x}$ $V_{ extsf{DDP}}$	_	-	V	$R_{\rm S} = 0$ Ohm
Absolute input leakage current on pins of analog ports ³⁾	I _{OZ1} CC	-	10	200	nA	$V_{\rm IN} > V_{\rm SS}; \\ V_{\rm IN} < V_{\rm DDP}$
Absolute input leakage current for all other pins. To be doubled for double	I _{OZ2} CC	-	0.2	2.5	μΑ	$T_{\rm J} \leq 110 ~^{\circ}{\rm C};$ $V_{\rm IN} < V_{\rm DDP};$ $V_{\rm IN} > V_{\rm SS}$
bond pins. ³⁾¹⁾⁴⁾		-	0.2	8	μA	$T_{\rm J} \leq 150 ~^{\circ}{\rm C};$ $V_{\rm IN} < V_{\rm DDP};$ $V_{\rm IN} > V_{\rm SS}$
Pull Level Force Current ⁵⁾	$ I_{PLF} $ SR	150	-	-		6)
Pull Level Keep Current ⁷⁾	I _{PLK} SR	-	_	10	μA	6)
Input high voltage (all except XTAL1)	$V_{\rm IH}{ m SR}$	$0.7 ext{ x}$ $V_{ ext{DDP}}$	-	V _{DDP} + 0.3	V	
Input low voltage (all except XTAL1)	$V_{IL} SR$	-0.3	-	$0.3 ext{ x}$ $V_{ ext{DDP}}$	V	
Output High voltage ⁸⁾	V _{OH} CC	V _{DDP} - 1.0	-	-	V	$I_{\rm OH} \ge I_{\rm OHmax}$
		V _{DDP} - 0.4	-	-	V	$I_{\rm OH} \ge I_{\rm OHnom}^{9)}$

Table 14 DC Characteristics for Lower Voltage Range



4.2.3 Power Consumption

The power consumed by the XE167xM depends on several factors such as supply voltage, operating frequency, active circuits, and operating temperature. The power consumption specified here consists of two components:

- The switching current $I_{\rm S}$ depends on the device activity
- The leakage current I_{LK} depends on the device temperature

To determine the actual power consumption, always both components, switching current $I_{\rm S}$ and leakage current $I_{\rm LK}$ must be added:

 $I_{\text{DDP}} = I_{\text{S}} + I_{\text{LK}}.$

Note: The power consumption values are not subject to production test. They are verified by design/characterization.

To determine the total power consumption for dimensioning the external power supply, also the pad driver currents must be considered.

The given power consumption parameters and their values refer to specific operating conditions:

Active mode:

Regular operation, i.e. peripherals are active, code execution out of Flash.

Stopover mode:

Crystal oscillator and PLL stopped, Flash switched off, clock in domain DMP_1 stopped.

Note: The maximum values cover the complete specified operating range of all manufactured devices.

The typical values refer to average devices under typical conditions, such as nominal supply voltage, room temperature, application-oriented activity.

After a power reset, the decoupling capacitors for $V_{\rm DDIM}$ and $V_{\rm DDI1}$ are charged with the maximum possible current.

For additional information, please refer to Section 5.2, Thermal Considerations.

Note: Operating Conditions apply.

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
Power supply current (active) with all peripherals active and EVVRs on	I _{SACT} CC	_	$10 + 0.6 x f_{SYS}^{1)}$	10 + 1.0 x f _{SYS} ¹⁾	mA	2)3)
Power supply current in stopover mode, EVVRs on	I _{SSO} CC	-	0.7	2.0	mA	

Table 15 Switching Power Consumption

1) $f_{\rm SYS}$ in MHz.



- 3) $f_{\rm WU}$ in MHz
- 4) This value includes a hysteresis of approximately 50 mV for rising voltage.
- 5) $V_{\rm LV}$ = selected SWD voltage level
- 6) The limit V_{LV} 0.10 V is valid for the OK1 level. The limit for the OK2 level is V_{LV} 0.15 V.

Conditions for t_{SPO} Timing Measurement

The time required for the transition from **Power-On** to **Base** mode is called t_{SPO} . It is measured under the following conditions:

Precondition: The pad supply is valid, i.e. V_{DDPB} is above 3.0 V and remains above 3.0 V even though the XE167xM is starting up. No debugger is attached.

Start condition: Power-on reset is removed ($\overline{PORST} = 1$).

End condition: External pin toggle caused by first user instruction executed from FLASH after startup.

Conditions for t_{SSO} Timing Measurement

The time required for the transition from **Stopover** to **Stopover Waked-Up** mode is called t_{SSO} . It is measured under the following conditions:

Precondition: The **Stopover** mode has been entered using the procedure defined in the Programmer's Guide.

Start condition: Pin toggle on ESR pin triggering the startup sequence.

Coding of bit fields LEVxV in SWD and PVC Configuration Registers

End condition: External pin toggle caused by first user instruction executed from PSRAM after startup.

l able 20	Coding of bit fields LEVx	V in Register SWDCON0
Code	Default Voltage Level	Notes ¹⁾
0000 _B	2.9 V	
0001 _B	3.0 V	LEV1V: reset request
0010 _B	3.1 V	
0011 _B	3.2 V	
0100 _B	3.3 V	
0101 _B	3.4 V	
0110 _B	3.6 V	
0111 _B	4.0 V	
1000 _B	4.2 V	

Table 20 Coding of bit fields LEVxV in Register SWDCON0



4.5 Flash Memory Parameters

The XE167xM is delivered with all Flash sectors erased and with no protection installed. The data retention time of the XE167xM's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Parameter	Symbol		Values	6	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Parallel Flash module program/erase limit	$N_{\rm PP}{ m SR}$	-	-	4 ¹⁾		$N_{\text{FL}_{\text{RD}}} \le 1,$ $f_{\text{SYS}} \le 80 \text{ MHz}$
depending on Flash read activity		-	-	1 ²⁾		$N_{\rm FL_RD}$ > 1
Flash erase endurance for security pages	$N_{\rm SEC}{ m SR}$	10	-	-	cycle s	$t_{RET} \ge 20$ years
Flash wait states3)	N _{WSFLAS} _H SR	1	-	-		$f_{SYS} \le 8 \text{ MHz}$
		2	-	-		$f_{SYS} \le 13 \text{ MHz}$
		3	-	-		$f_{\rm SYS} \le 17 \ \rm MHz$
		4	-	-		$f_{\rm SYS}$ > 17 MHz
Erase time per sector/page	t _{ER} CC	-	7 ⁴⁾	8.0	ms	
Programming time per page	t _{PR} CC	-	34)	3.5	ms	
Data retention time	t _{RET} CC	20	-	-	year s	$N_{\rm Er} \le 1\ 000$ cycles
Drain disturb limit	$N_{\rm DD}{ m SR}$	32	-	-	cycle s	

Table 22 Flash Parameters



4.6 AC Parameters

These parameters describe the dynamic behavior of the XE167xM.

4.6.1 Testing Waveforms

These values are used for characterization and production testing (except pin XTAL1).

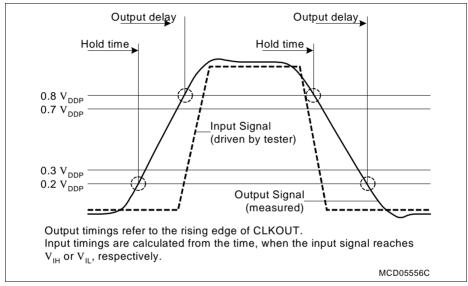
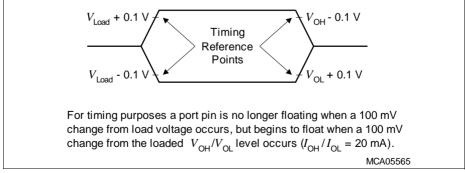


Figure 17 Input Output Waveforms







Direct Drive

When direct drive operation is selected (SYSCON0.CLKSEL = 11_B), the system clock is derived directly from the input clock signal CLKIN1:

 $f_{SYS} = f_{IN}$.

The frequency of f_{SYS} is the same as the frequency of f_{IN} . In this case the high and low times of f_{SYS} are determined by the duty cycle of the input clock f_{IN} .

Selecting Bypass Operation from the XTAL1¹⁾ input and using a divider factor of 1 results in a similar configuration.

Prescaler Operation

When prescaler operation is selected (SYSCON0.CLKSEL = 10_B , PLLCON0.VCOBY = 1_B), the system clock is derived either from the crystal oscillator (input clock signal XTAL1) or from the internal clock source through the output prescaler K1 (= K1DIV+1):

 $f_{\text{SYS}} = f_{\text{OSC}} / \text{K1}.$

If a divider factor of 1 is selected, the frequency of $f_{\rm SYS}$ equals the frequency of $f_{\rm OSC}$. In this case the high and low times of $f_{\rm SYS}$ are determined by the duty cycle of the input clock $f_{\rm OSC}$ (external or internal).

The lowest system clock frequency results from selecting the maximum value for the divider factor K1:

 $f_{\rm SYS} = f_{\rm OSC} / 1024.$

4.6.2.1 Phase Locked Loop (PLL)

When PLL operation is selected (SYSCON0.CLKSEL = 10_B , PLLCON0.VCOBY = 0_B), the on-chip phase locked loop is enabled and provides the system clock. The PLL multiplies the input frequency by the factor **F** ($f_{SYS} = f_{IN} \times F$).

F is calculated from the input divider P (= PDIV+1), the multiplication factor N (= NDIV+1), and the output divider K2 (= K2DIV+1):

 $(F = N / (P \times K2)).$

The input clock can be derived either from an external source at XTAL1 or from the onchip clock source.

The PLL circuit synchronizes the system clock to the input clock. This synchronization is performed smoothly so that the system clock frequency does not change abruptly.

Adjustment to the input clock continuously changes the frequency of f_{SYS} so that it is locked to f_{IN} . The slight variation causes a jitter of f_{SYS} which in turn affects the duration of individual TCSs.

¹⁾ Voltages on XTAL1 must comply to the core supply voltage V_{DDIM} .



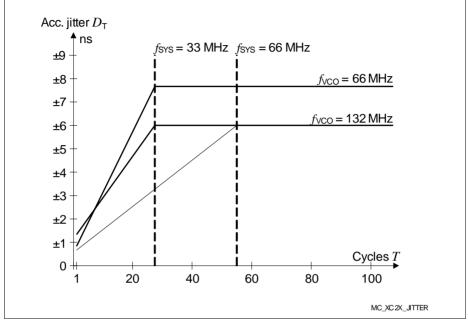


Figure 20 Approximated Accumulated PLL Jitter

Note: The specified PLL jitter values are valid if the capacitive load per pin does not exceed $C_L = 20 \text{ pF}$.

The maximum peak-to-peak noise on the pad supply voltage (measured between V_{DDPB} pin 100 and V_{SS} pin 1) is limited to a peak-to-peak voltage of V_{PP} = 50 mV. This can be achieved by appropriate blocking of the supply voltage as close as possible to the supply pins and using PCB supply and ground planes.



 Table 26 is valid under the following conditions:

 $V_{\text{DDP}} \ge 3.0 \text{ V}; V_{\text{DDPtyp}} = 3.3 \text{ V}; V_{\text{DDP}} \le 4.5 \text{ V}; C_{\text{L}} \ge 20 \text{ pF}; C_{\text{L}} \le 100 \text{ pF};$

Table 26	Standard Pad Parameters for Lower Voltage Range
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Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.	1	Test Condition
Maximum output driver current (absolute value) ¹⁾	I _{Omax} CC	-	-	10	mA	Strong driver
		_	-	2.5	mA	Medium driver
		-	-	0.5	mA	Weak driver
Nominal output driver current (absolute value)	I _{Onom} CC	-	-	2.5	mA	Strong driver
		_	-	1.0	mA	Medium driver
		-	-	0.1	mA	Weak driver
Rise and Fall times (10% - 90%)	t _{RF} CC	-	-	6.2 + 0.24 x <i>C</i> _L	ns	Strong driver; Sharp edge
		-	-	24 + 0.3 x C _L	ns	Strong driver; Medium edge
		-	-	34 + 0.3 x C _L	ns	Strong driver; Slow edge
		_	-	37 + 0.65 x <i>C</i> L	ns	Medium driver
		-	-	500 + 2.5 x <i>C</i> L	ns	Weak driver

 The total output current that may be drawn at a given time must be limited to protect the supply rails from damage. For any group of 16 neighboring output pins, the total output current in each direction (ΣI_{OL} and Σ-I_{OH}) must remain below 50 mA.



Electrical Parameters

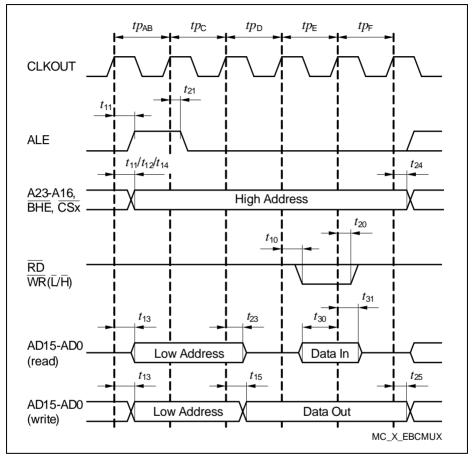


Figure 23 Multiplexed Bus Cycle



4.6.5.1 Bus Cycle Control with the READY Input

The duration of an external bus cycle can be controlled by the external circuit using the READY input signal. The polarity of this input signal can be selected.

Synchronous READY permits the shortest possible bus cycle but requires the input signal to be synchronous to the reference signal CLKOUT.

An asynchronous READY signal puts no timing constraints on the input signal but incurs a minimum of one waitstate due to the additional synchronization stage. The minimum duration of an asynchronous READY signal for safe synchronization is one CLKOUT period plus the input setup time.

An active READY signal can be deactivated in response to the trailing (rising) edge of the corresponding command (\overline{RD} or \overline{WR}).

If the next bus cycle is controlled by READY, an active READY signal must be disabled before the first valid sample point in the next bus cycle. This sample point depends on the programmed phases of the next cycle.



Electrical Parameters

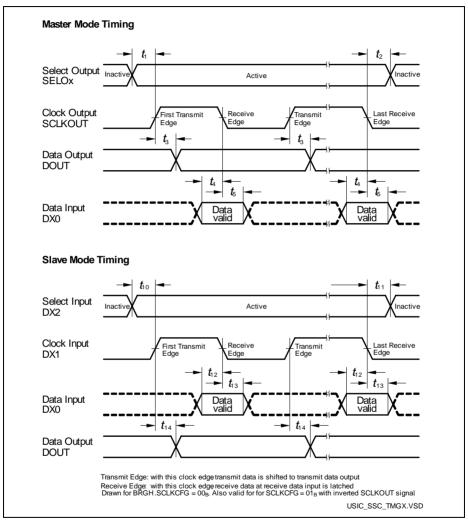


Figure 28 USIC - SSC Master/Slave Mode Timing

Note: This timing diagram shows a standard configuration where the slave select signal is low-active and the serial clock signal is not shifted and not inverted.



Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
DAP0 clock period	<i>t</i> ₁₁ SR	25 ¹⁾	-	-	ns	
DAP0 high time	t ₁₂ SR	8	-	-	ns	
DAP0 low time	t ₁₃ SR	8	-	_	ns	
DAP0 clock rise time	t ₁₄ SR	-	-	4	ns	
DAP0 clock fall time	t ₁₅ SR	-	-	4	ns	
DAP1 setup to DAP0 rising edge	<i>t</i> ₁₆ SR	6	-	-	ns	pad_type= stan dard
DAP1 hold after DAP0 rising edge	<i>t</i> ₁₇ SR	6	-	-	ns	pad_type= stan dard
DAP1 valid per DAP0 clock period ²⁾	<i>t</i> ₁₉ CC	12	17	-	ns	pad_type= stan dard

Table 38 DAP Interface Timing for Lower Voltage Range

1) The debug interface cannot operate faster than the overall system, therefore $t_{11} \ge t_{SYS}$.

2) The Host has to find a suitable sampling point by analyzing the sync telegram response.

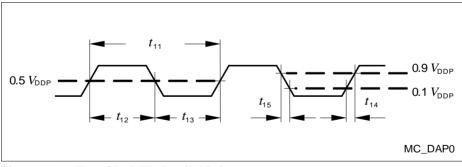


Figure 29 Test Clock Timing (DAP0)